

PTO-1449

Application No.

09 736,043

Applicant(s)

Yue (mni) Kuo

**Information Disclosure Citation  
In an Application**

Docket Number

01 7575,0414

Group Art Unit

2823

Filing Date

12 12 2000

(TAMUS 1529)

**U.S. PATENT DOCUMENTS**

DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
A					
B					

**FOREIGN PATENT DOCUMENTS**

DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
					YES NO

DOCUMENT (Including Author, Title, Source, and Pertinent Pages)					DATE
C		"Control Using $Cl_2$ Gas as a Single Reactant," J. Vac. Sci. Technol. B, 15 (2), p. 237			1997
D		"National Technology Roadmap for Semiconductors (NTRS)," Semiconductor Industry Association (SIA)			1997
E		H. Miyazaki, et al., "Copper Dry Etching with Precise Wafer-temperature Control Using $Cl_2$ Gas as a Single Reactant," J. Vac. Sci. Technol. B, 15 (2), p. 237			1997
F		J.W. Lee, et al., "Copper Dry Etching with $Cl_2$ Ar Plasma Chemistry," J. Electrochem. Soc., 145 (7), p. 2585			1998
G		Y. Ohshita, et al., "Lower Temperature Plasma Etching of Cu Using IR Light Irradiation," Thin Solid Films, 262, p. 67			1995
H		G.C. Schwartz, et al., "Reactive Ion Etching of Copper Films," J. Electrochem. Soc., 130, p. 1777			1983
I		B.J. Howard, et al., "Reactive Ion Etching of Copper in $SiCl_4$ -based Plasmas," Appl. Phys. Lett., 59, p. 914			1991
J		M. Markert, et al., "Copper Dry Etching Technique for ULSI Interconnections," Microelectronic Engineering, 35, p. 333			1997
K		IBM Journal of Research and Development, special issue on Plasma Processing, Guest editor, Y. Kuo, 43(1 2)			1999
L		Sangheon Lee, et al., "Process Study of a New Copper Dry Etching Method - The HCL Chemistry," Electrochem. Soc. Plasma Processing XIII Proceedings			2000
M		Sangyu Lee, et al., "Amorphous Silicon Thin Film Transistor Fabricated with a New Copper Dry Etching Method," Procs. ECS TFTTV Symp., Phoenix AZ, pp. 34-39			2001
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U		Yue Kuo, et al., "[190i] - A Reactive Ion Etching Based Copper Etch Process," American Institute of Chemical Engineers, www.aiche.org/conferences/techpro...aperdetail.asp?PaperID=3270&DSN=annual99			1999

EXAMINER

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EXAMINER: *mic 2/1/03* DATE CONSIDERED: *3/19/03*

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